XN0NE92

Silicon P-channel MOSFET (FET) Silicon epitaxial planar type (SBD)

For DC-DC converter

■ Features

- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half
- High-speed switching, low on resistance

■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit	3: Gate
FET	Drain-source surrender	V _{DSS}	-12	V	- Marking C
	voltage				■ Marking S
	Gate-source surrender	V _{GSS}	±15	V	
	voltage				Internal C
	Drain current	I_D	-1.2	A	
	Peak drain current	I_{DP}	-3	A	
	Total power dissipation *	P _T	600	mW	لے `
	Channel temperature	T_{ch}	125	°C	× Ø
	Storage temperature	T_{stg}	-55 to +125	°C	asonic reals
SBD	Reverse voltage	V_R	20	V	
	Repetitive peak reverse voltage	V _{RRM}	25	V	200 esti
	Forward current (Average)	I _{F(AV)}	700	mA	
	Non-repetitive peak	I _{FSM}	2	A	is allo
	forward surge current				°0,
Note) *:	Measuring on ceramic substrate	e at 15 mm	$1 \times 15 \text{ mm} \times 0$.6 mm	D.
			. 6	71, OS.	
■ Elec	trical Characteristics T	$C_a = 25^{\circ}C$	$C \pm 3^{\circ}C$://4	
• FET			ix YO .	gO.	
	Parameter	Symbo	\$	Conditions	Mir
Drain-source surrender voltage		Voss	$I_C = -1 \text{ m/s}$	$A, V_{GS} = 0$	-12
Drain-source cutoff current		I_{DSS}	$V_{DS} = -10$	$V, V_{GS} = 0$	
Gate-so	ource cutoff current	I_{GSS}	$V_{GS} = \pm 8$	$V, V_{DS} = 0$	
Gate threshold voltage		V.	$V_{pq} = -10$	V I _n = -1 m/	4 -0

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	VDss	$I_C = -1 \text{ mA}, V_{GS} = 0$	-12			V
Drain-source cutoff current	$\mathcal{I}_{\mathrm{DSS}}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0$			-1	V
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$			±10	V
Gate threshold voltage	V _{th}	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$	- 0.4		-1.3	V
Forward transfer admittance *	Yfs	$V_{DS} = -10 \text{ V}, I_{D} = -800 \text{ mA}$	0.8	1.1		S
Drain-source ON resistance *	R _{DS(on)}	$V_{GS} = -4 \text{ V}, I_D = -800 \text{ mA}$		350	450	mΩ
Turn-on time	t _{on}	$V_{DD} = -10 \text{ V}, R_L = 12.5 \Omega,$		15		ns
Storage time	t _{stg}	$I_D = -800 \text{ mA}, V_{GS} = 0 \text{ V to } -4 \text{ V}$		10		ns
Turn-off time	t _{off}			10		ns

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
 - 2. Observe precautions for handling. Electrostatic sensitive devices.
 - 3. *: Pulse measurement

Package

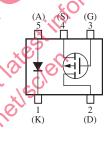
• Code Mini5-G1 (Exclusive use for XN0NE92)

Pin Name

1: Cathode 4: Source 2: Drain 5: Anode 3: Gate

■ Marking Symbol: 3F

■ Internal Connection



Publication date: April 2008 SJJ00308BED

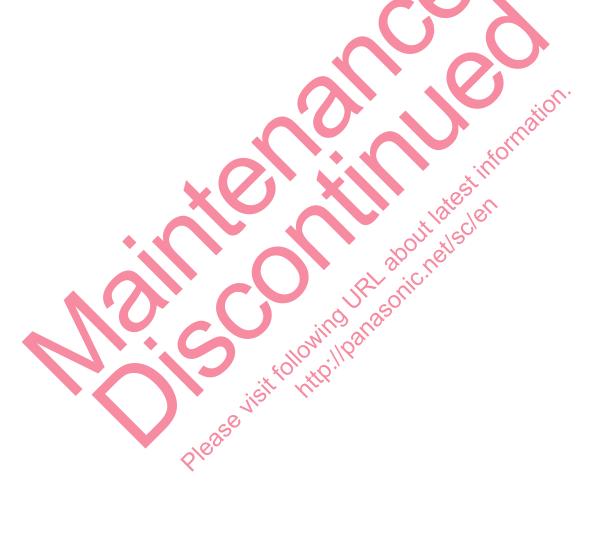
■ Electrical Characteristics (continued) $T_a = 25$ °C ± 3 °C

• SBD

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	V _F	$I_F = 700 \text{ mA}$			0.45	V
Reverse current	I_R	$V_R = 20 \text{ V}$			200	μΑ
Terminal capacitance	C_{t}	$V_R = 0$, $f = 1$ MHz		100		pF
Reverse recovery time	t _{rr}	$I_F = I_R = 100 \text{ mA}$		7		ns
		$I_{rr} = 10 \text{ mA}, R_L = 100 \Omega$				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

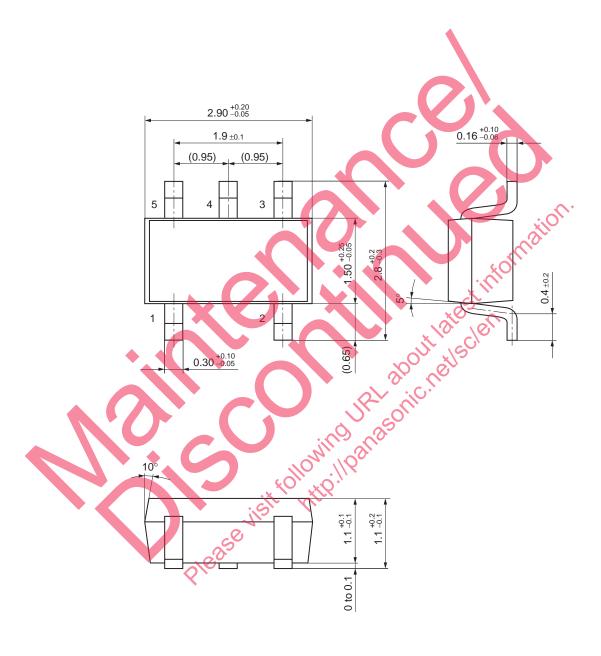
2. Schottky barrier diode is frail with static electricity, and it should be kept in safety from shock of static electricity and static electricity level.



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Mini5-G1 (Exclusive use for XN0NE92)

Unit: mm



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